

Predictive modeling of self-catalyzed GaAs nanowire growth

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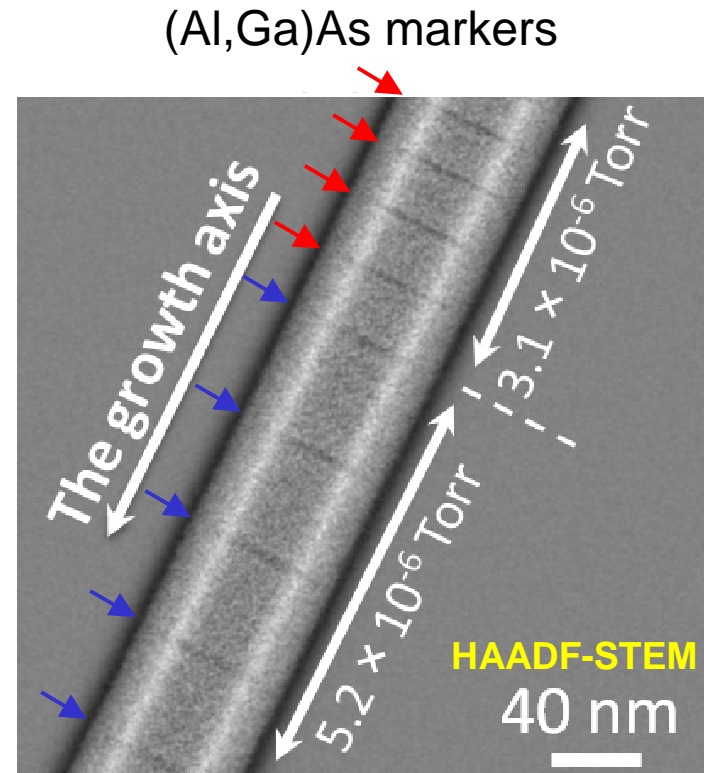
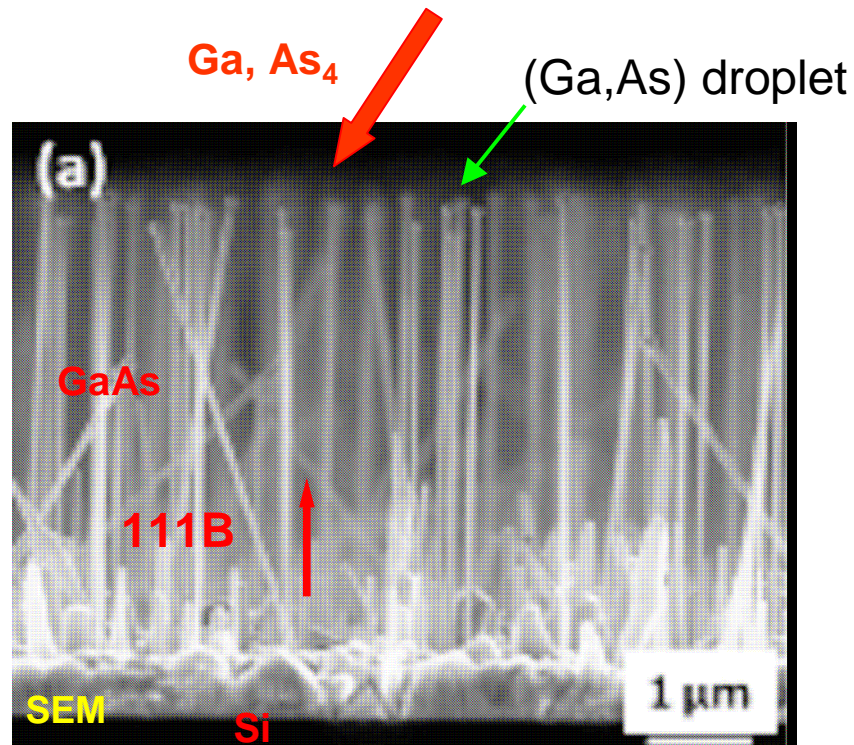
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Chronology of self-catalyzed GaAs growth

GaAs NWs by VLS MBE



- Cubic ZB structure
- No radial growth

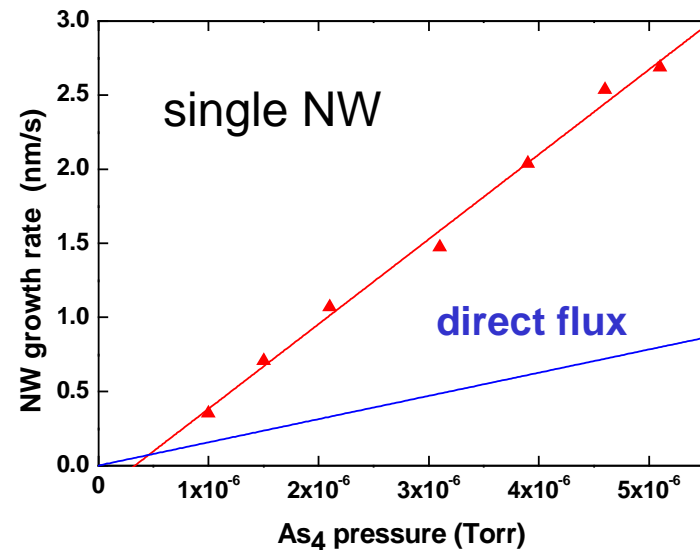
Ramdani, Harmand, Glas, Patriarche, Travers, NWG 2012, St Petersburg
Ramdani, Harmand, Glas, Patriarche, Travers, Cryst. Growth Des. 13, 91 (2013)

The mystery of the missing arsenic

❑ NW growth rate

- is independent of Ga flux
- varies linearly with As flux

Colombo et al., Phys. Rev. B 77, 155326 (2008)

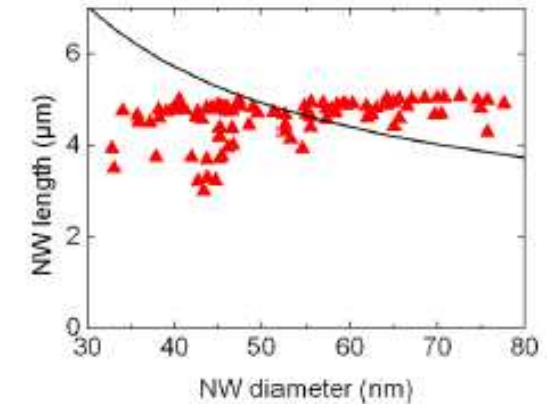
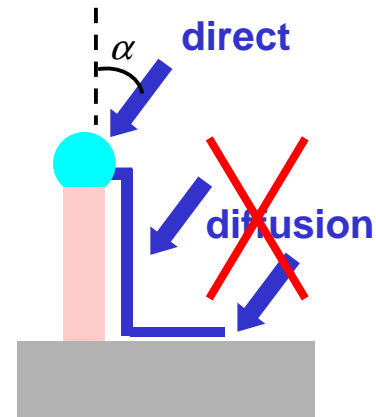


Ramdani et al., Cryst. Growth Des. 13, 91 (2013)

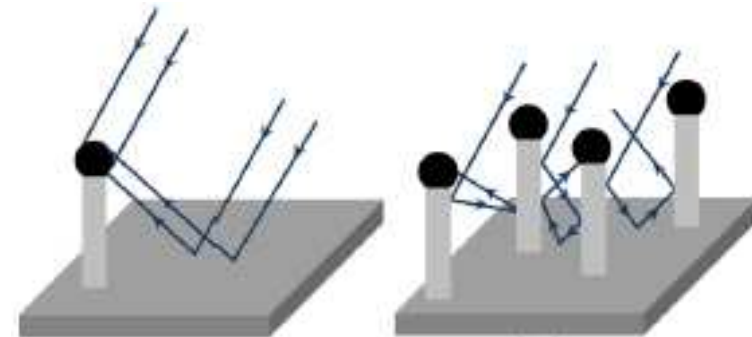
❑ Direct As flux is insufficient

$$\phi_d = \eta p_{As_4}$$

❑ As diffusion is negligible



❑ Missing As: re-emission?



As-only model

- ❑ Growth is governed by As
- ❑ Surface diffusion of As species can be neglected
- ❑ Droplet = (As,Ga) liquid
Thermodynamics entirely determined by c_{As} ($c_{\text{Ga}} = 1 - c_{\text{As}}$)

Find As concentration c_{As} in droplet

Model and experiments

$$\rho_d = \frac{a^3}{4 \sin^2 \beta} \eta p_{\text{As}_4}$$

$$\rho_e = k_e \frac{1 - \cos \beta}{\sin^2 \beta} \frac{a^3}{\sqrt{2\pi M k_B T}} p_{\text{As}_2}^{\text{eq}}(c_{\text{As}}, T)$$

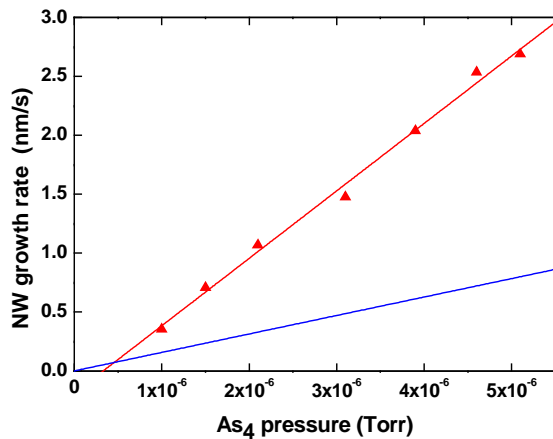
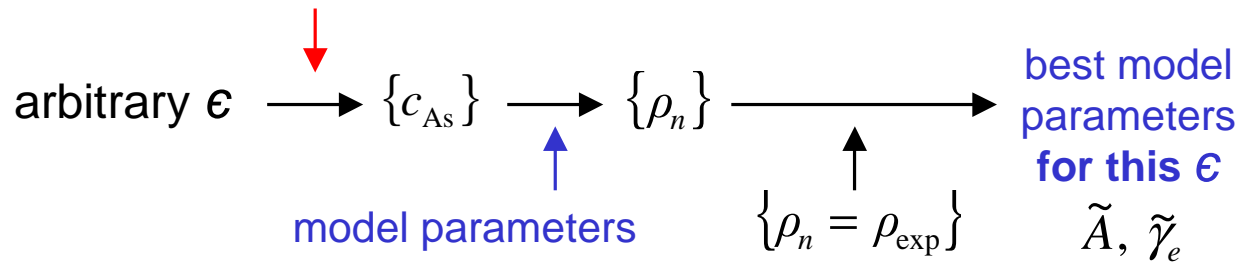
$$\rho_r = \epsilon \rho_d$$

$$\rho_n = \frac{dL}{dt} = \pi R^2 \frac{a}{\sqrt{3}} A(T) c_{\text{As}} \sqrt{\frac{\Delta\mu}{k_B T}} \exp\left[-\frac{\Delta G_c}{k_B T}\right]$$

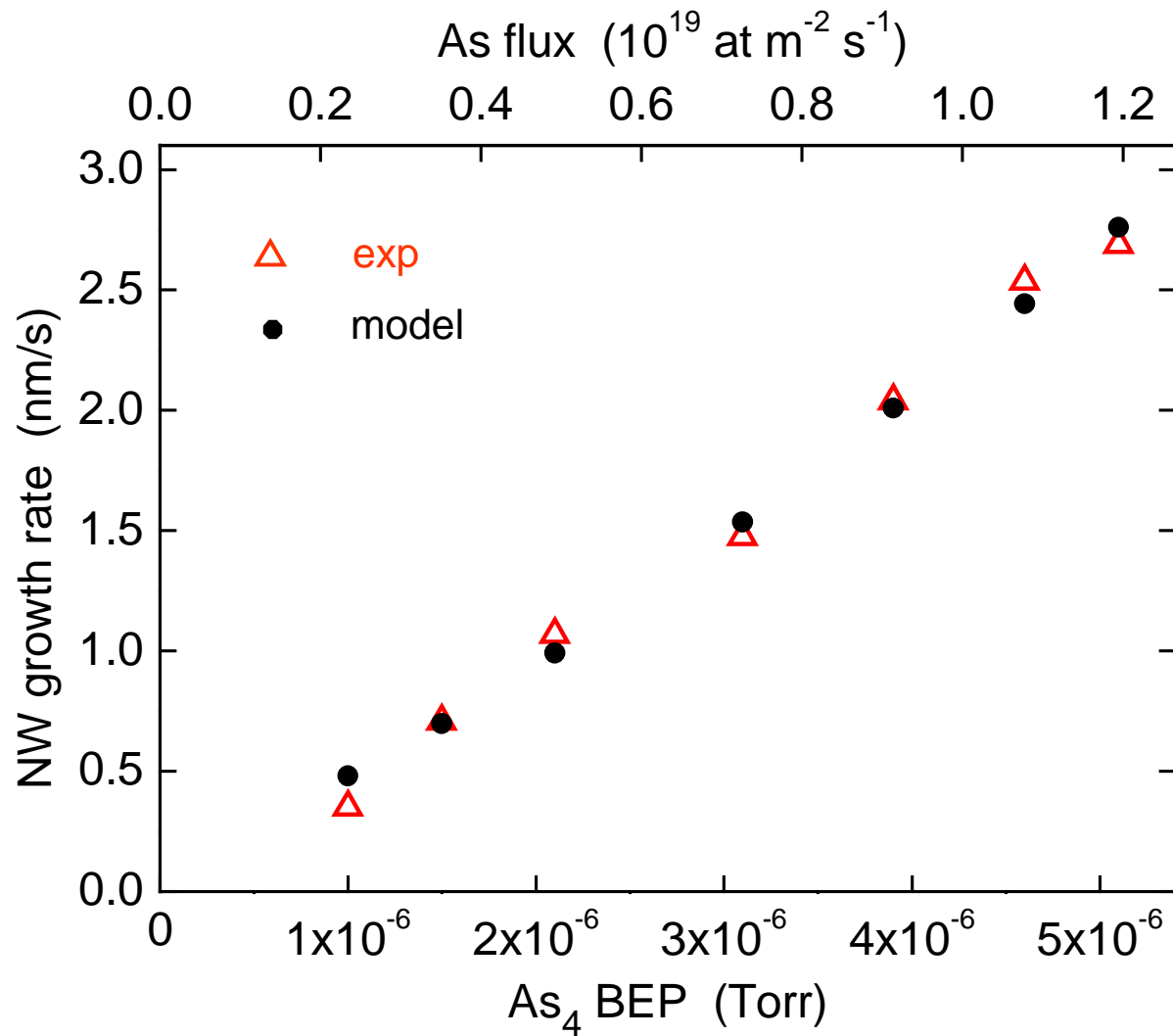
$$\Delta G_c = \chi \frac{a^4}{4\sqrt{3}} \frac{\gamma_e^2}{\Delta\mu(c_{\text{As}}, T)}$$

2 model parameters

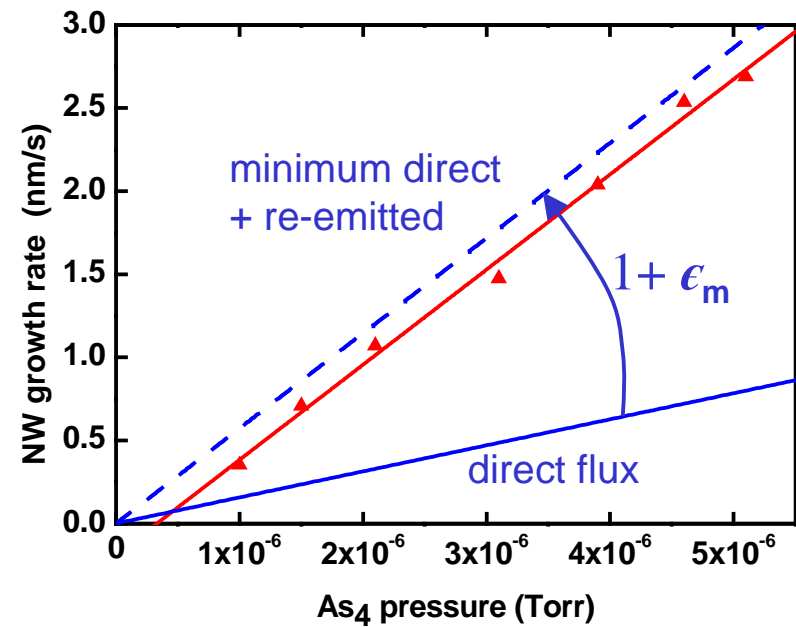
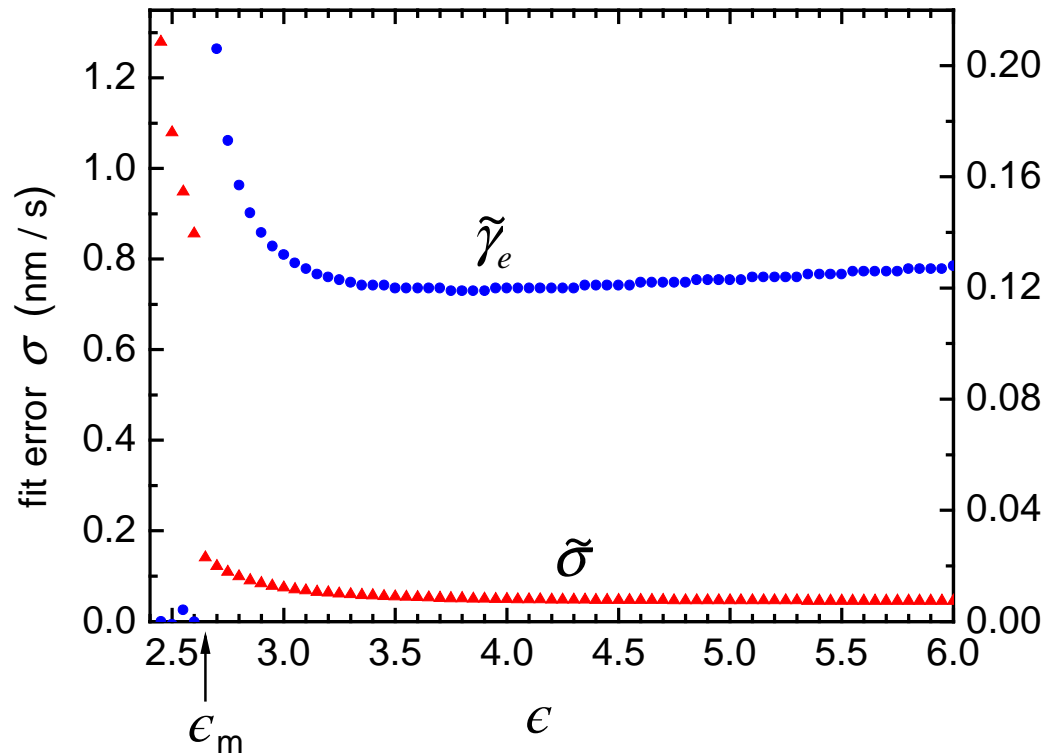
As material balance (drop) $(1 + \epsilon) \rho_d = \rho_e(c_{\text{As}}, T) + \rho_{\text{exp}}$



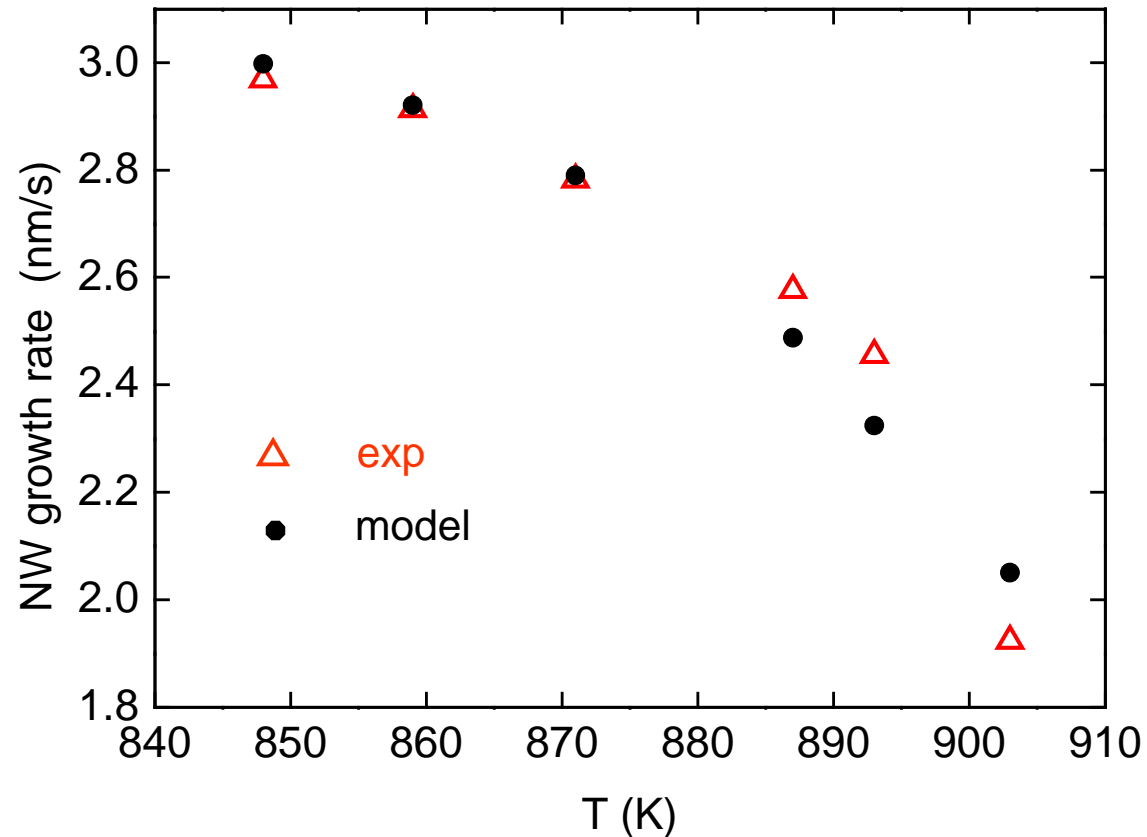
Fitting pressure series



Fitting pressure series - Minimum ϵ

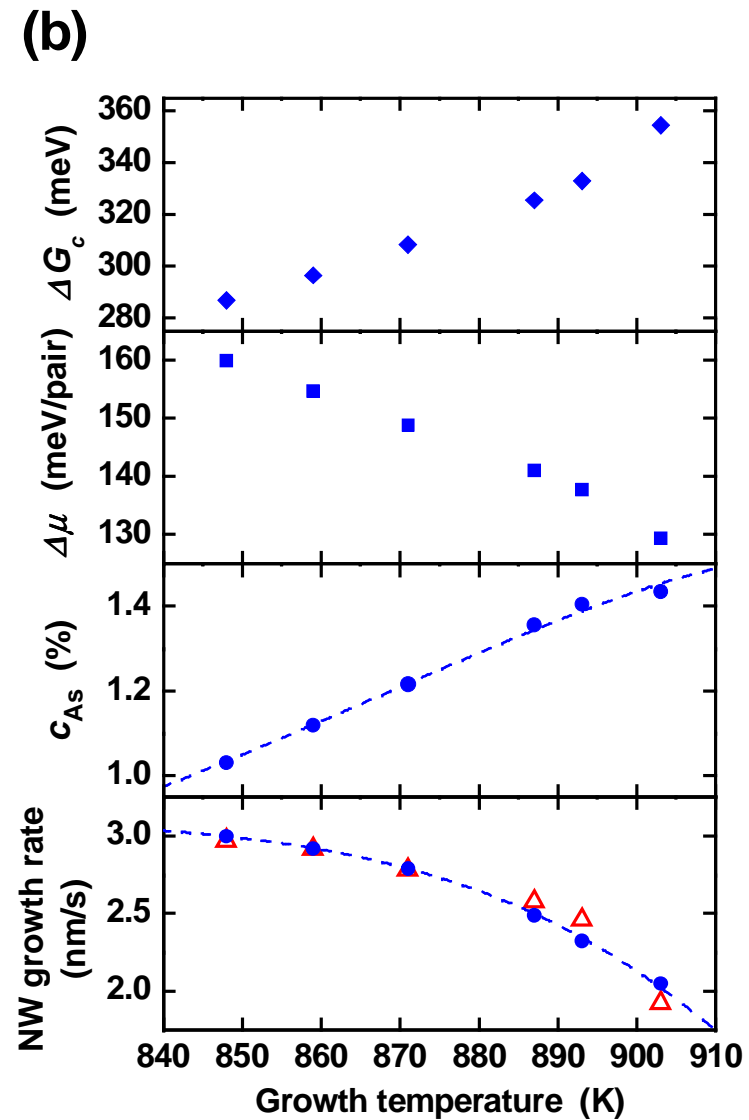
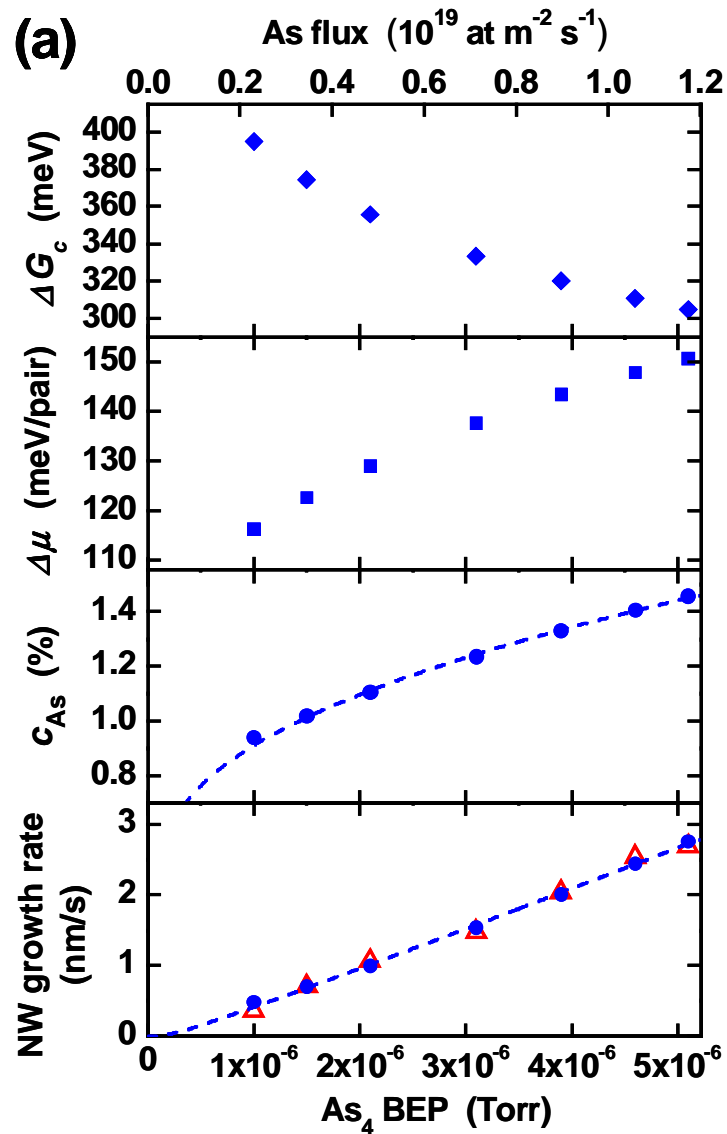


Fitting temperature series

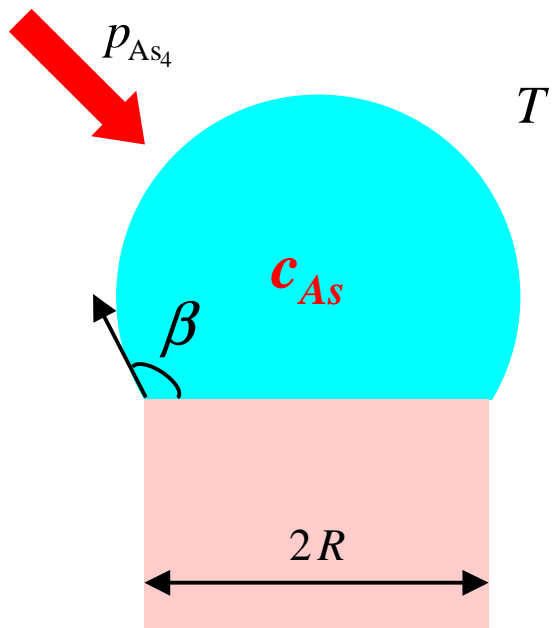


- Best values of model parameters $\gamma_e \approx 0.123 \text{ J/m}^2$
- Re-emission coefficient ϵ for individual NWs

Non-measurable quantities



Predictive modeling



As material balance

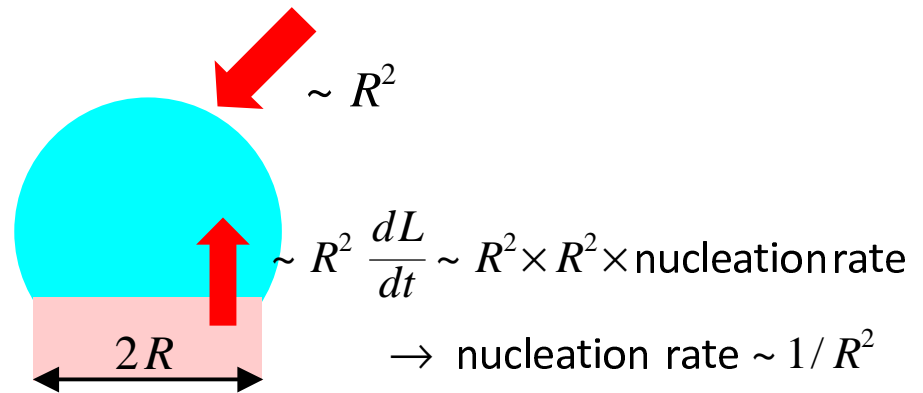
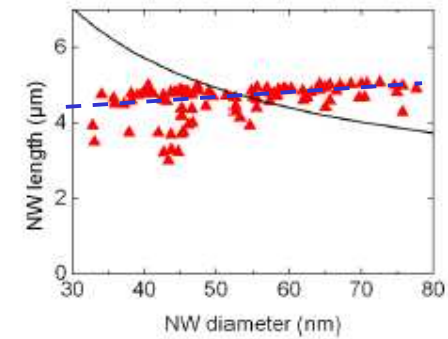
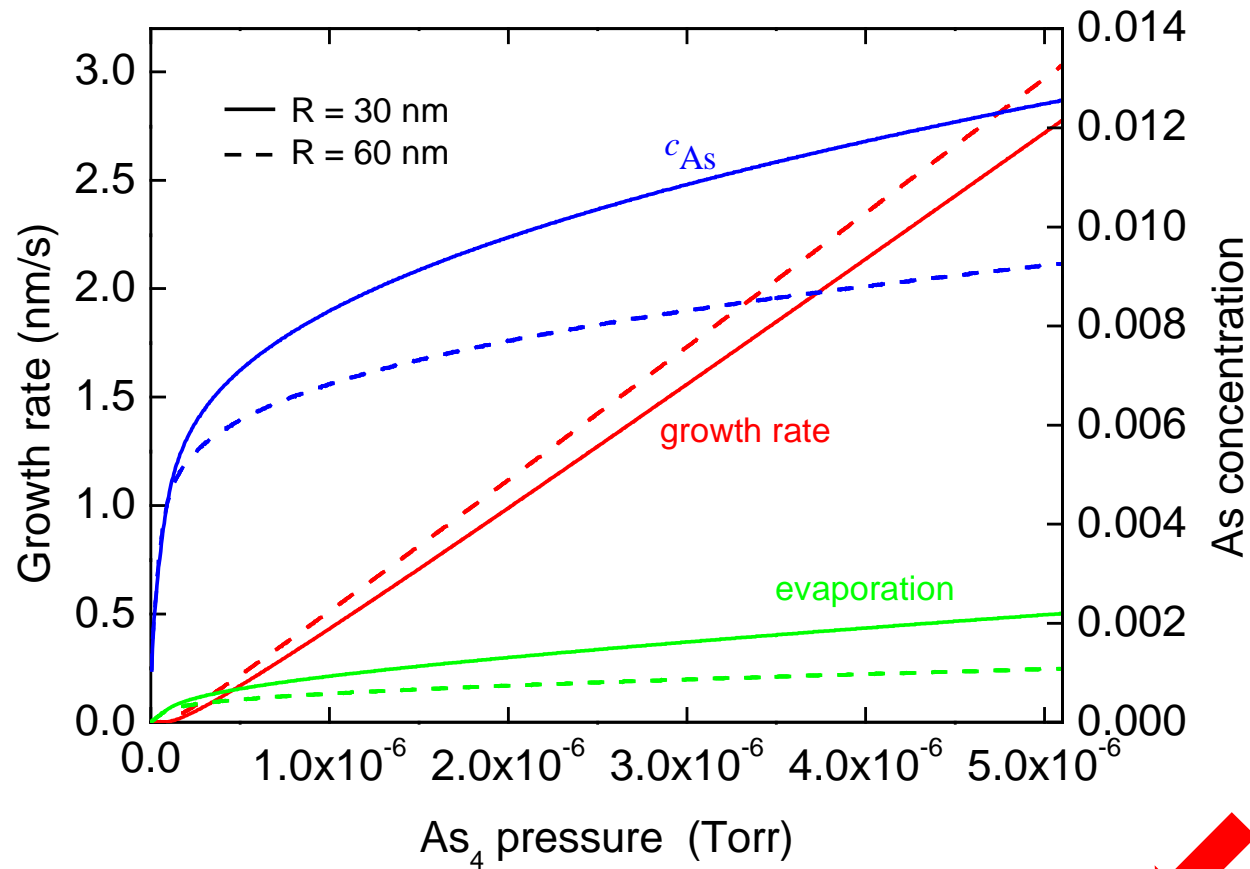
known

$$\rho_n = \pi R^2 \frac{a}{\sqrt{3}} A(T) c_{As} \sqrt{\frac{\Delta\mu}{k_B T}} \exp\left[-\chi \frac{a^3}{4\sqrt{3}} \frac{\gamma_e^2}{\Delta\mu k_B T}\right]$$

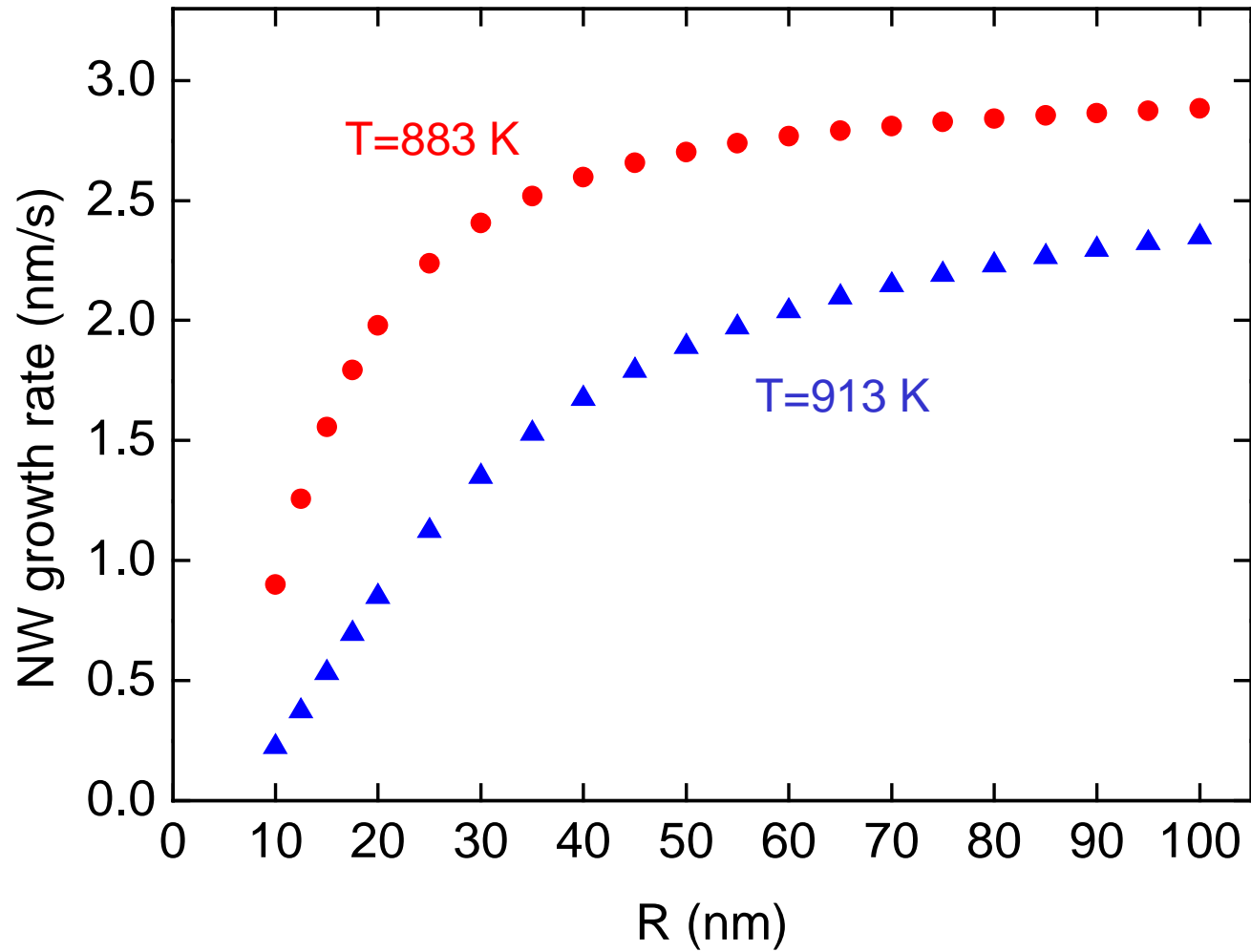
$c_{As}?$

$$(1+\epsilon) \rho_d = \rho_e(c_{As}, T) + \rho_n(c_{As}, T)$$

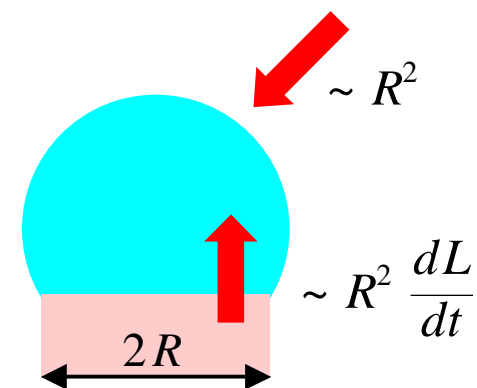
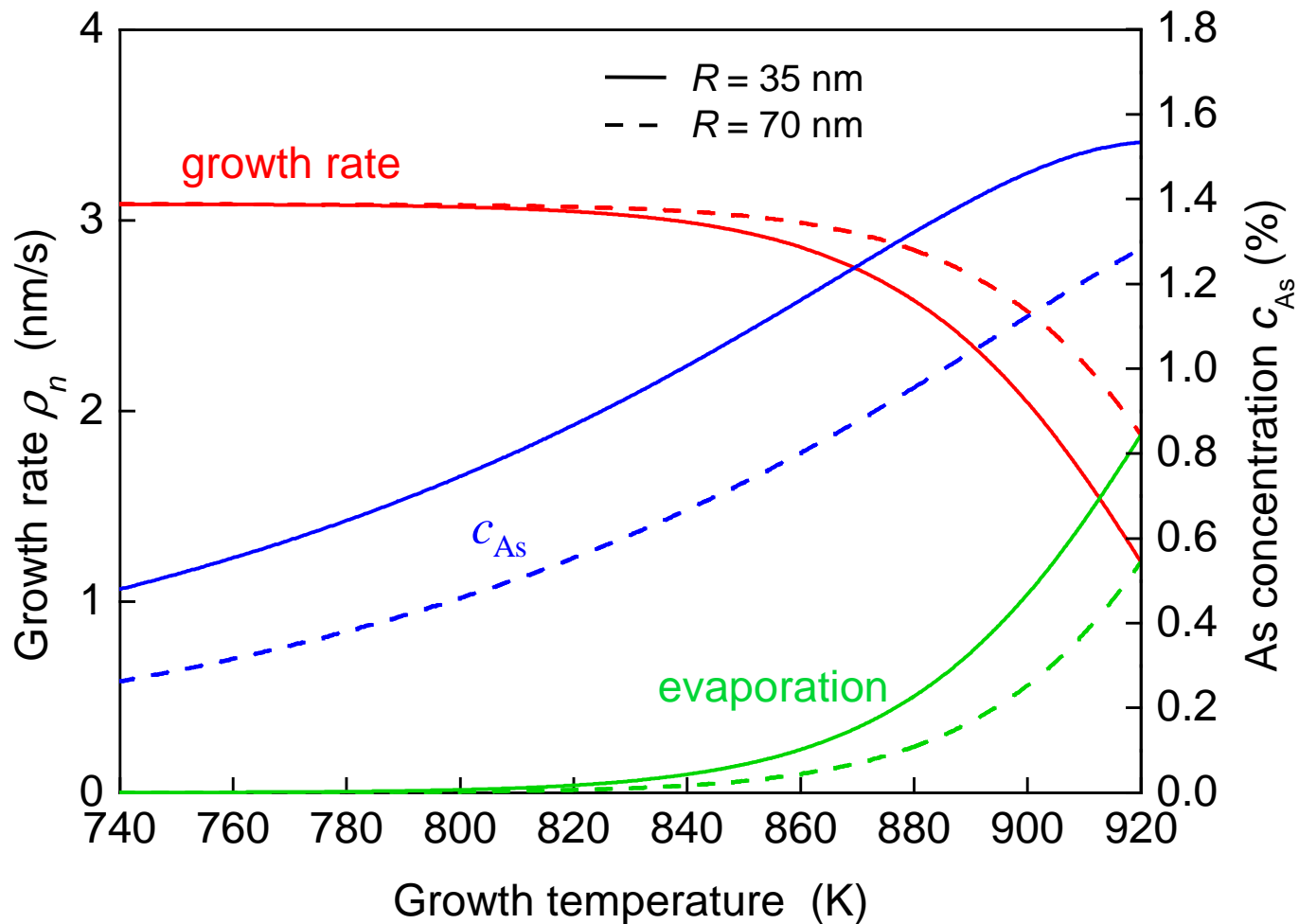
Simulated pressure series



Effect of NW radius



Simulated temperature series



Summary and conclusions

- ❑ As-only model for self-catalyzed GaAs NW growth
- ❑ Values of model parameters

$$\gamma_e \approx 0.123 \pm 0.02 \text{ J/m}^2$$

$$\text{Hurle, J. Cryst. Growth 147, 239 (1995)} \quad \gamma_e = 0.119 \text{ J/m}^2 \quad \gamma_e = 0.064 \text{ J/m}^2 \text{ (InP)}$$

- ❑ Values of non-measurable quantities for single NWs

$$c_{\text{As}} \sim 1\% \quad \Delta\mu \quad \Delta G_c \quad \epsilon$$

- ❑ Model predicts NW growth rate and thermodynamic state of the droplet in given growth conditions (As flux, T , ϵ)

Glas, Ramdani, Patriarche, Harmand, Phys. Rev. B 88, 195304 (2013)